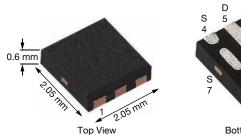
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Vishay Siliconix

N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A) ^{b, c}	Q _g (Typ.)						
20	0.0135 at V _{GS} = 10 V	12 ^a	5.3 nC						
	0.0185 at V _{GS} = 4.5 V	10.8	5.5110						

Thin PowerPAK[®] SC-70-6L Single



SiA430DJT-T1-GE3 (Lead (Pb)-free and halogen-free)

Marking Code: AY **Ordering Information:**



Bottom View

FEATURES

- TrenchFET[®] power MOSFET
- Thermally enhanced PowerPAK® SC-70 package - Small footprint area
 - Ultra-thin 0.6 mm height
- 100 % R_a tested

· Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- · Load switch
- DC/DC conversion



N-Channel MOSFET

ABSOLUTE MAXIMUM RATING	S (T _A = 25 °C, u	inless otherv	vise noted)			
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	20	V		
Gate-Source Voltage	V _{GS}	± 20	v			
	T _C = 25 °C		12 ^a			
Continuous Drain Current (T. 150 °C)	T _C = 70 °C	1	12 ^a			
Continuous Drain Current ($T_J = 150 \ ^\circ C$)	T _A = 25 °C	I _D	12 ^{a, b, c}			
	T _A = 70 °C	1	10.1 ^{b, c}	A		
Pulsed Drain Current (t = 100 µs)	I _{DM}	40				
Continuous Source-Drain Diode Current	T _C = 25 °C		12 ^a			
Continuous Source-Drain Diode Current	T _A = 25 °C	- I _S	2.9 ^{b, c}			
	T _C = 25 °C		19.2			
Meximum Dever Dissinction	T _C = 70 °C		12.3	w		
Maximum Power Dissipation	T _A = 25 °C	P _D	3.5 ^{b, c}	vv		
	T _A = 70 °C	1	2.2 ^{b, c}			
Operating Junction and Storage Temperatur	T _J , T _{stg}	-55 to +150	℃			
Soldering Recommendations (Peak Tempera		260	U U			

THEDMAL DEGISTANCE DATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT					
Maximum Junction-to-Ambient b, f	t ≤ 5 s	R _{thJA}	28	36	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	5.3	6.5	0/10				

Notes

a. Package limited

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (www.vishay.com/doc?73257). The Thin PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.

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Document Number: 62991

For technical questions, contact: pmostechsupport@vishay.com

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RoHS COMPLIANT

HALOGEN





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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static		•				
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$	20	-	-	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	L 050 A	-	24	-	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-5.6	-	mV/°C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	1	-	3	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$	-	-	± 100	nA
Zaus Osta Malta na Dusia Ourrant		$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1	μA
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 ^{\circ}\text{C}$	-	-	10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	20	-	-	Α
Ducia Course On Otata Decistance 2		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 7 \text{ A}$	-	0.0108	0.0135	0
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 5 \text{ A}$	-	- 0.0146	0.0185	Ω
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 7 \text{ A}$	-	16	-	S
Dynamic ^b		•				
Input Capacitance	C _{iss}		-	800	-	
Output Capacitance	C _{oss}	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$	-	200	-	pF
Reverse Transfer Capacitance	C _{rss}		-	90	-	
Tatal Cata Charge	Qg	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 12 \text{ A}$	-	12	18	nC
Total Gate Charge			-	5.3	9	
Gate-Source Charge Q _{gs}		$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 12 \text{ A}$	-	2	-	ne
Gate-Drain Charge	Q _{gd}		-	1.4	-	1
Gate Resistance	R _g	f = 1 MHz	0.5	2.5	5	Ω
Turn-On Delay Time	t _{d(on)}		-	16	25	
Rise Time	t _r	V_{DD} = 10 V, R_L = 1 Ω	-	10	15	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 10 A, V_{GEN} = 4.5 V, R_g = 1 Ω	-	15	25	
Fall Time	t _f		-	10	15	
Turn-On Delay Time t _{d(on)}			-	10	15	ns
Rise Time	t _r	V_{DD} = 10 V, R_L = 1 Ω	-	8	15	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω	-	17	30	
Fall Time	t _f		-	8	15	
Drain-Source Body Diode Characteristic	s					
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	12	А
Pulse Diode Forward Current (t = 100 µs)	I _{SM}		-	-	40	A
Body Diode Voltage	V_{SD}	$I_{\rm S} = 5$ A, $V_{\rm GS} = 0$ V	-	0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}		-	18	30	ns
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 10 A, di/dt = 100 A/µs, T,I = 25 °C	-	7	15	nC
Reverse Recovery Fall Time	t _a	$I_F = 10 \text{ A}, \text{ al/al} = 100 \text{ A/} \mu \text{s}, \text{ I}_J = 25 ^{\circ}\text{C}$	-	8	-	
Reverse Recovery Rise Time	t _b		-	10	-	ns

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

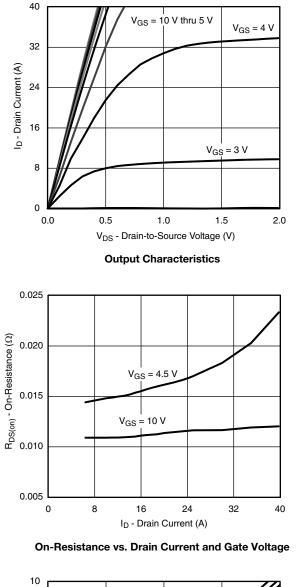
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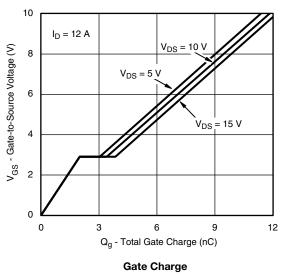
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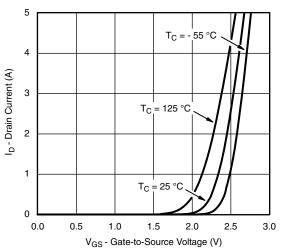
SiA430DJT

Vishay Siliconix

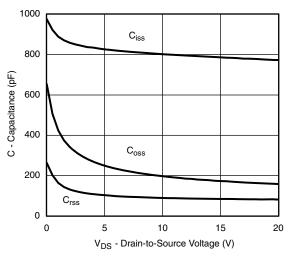
TYPICAL CHARACTERISTICS (T_J = 25 °C, unless otherwise noted)



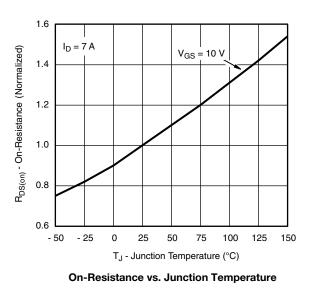




Transfer Characteristics







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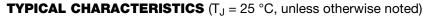
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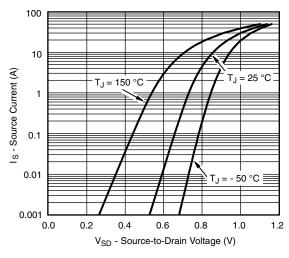
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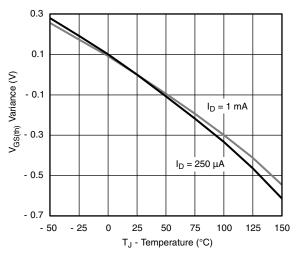
SiA430DJT

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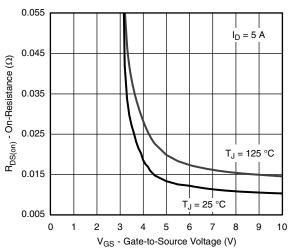




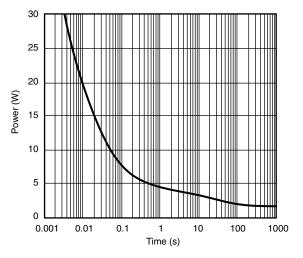
Source-Drain Diode Forward Voltage



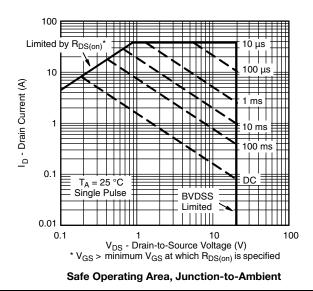




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power (Junction-to-Ambient)



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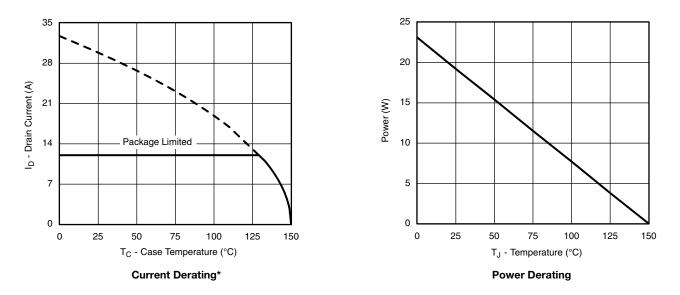
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TYPICAL CHARACTERISTICS (T_J = 25 °C, unless otherwise noted)

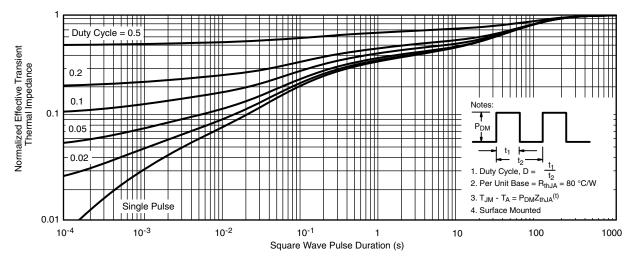


* The power dissipation P_D is based on $T_{J (max.)} = 150 \text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

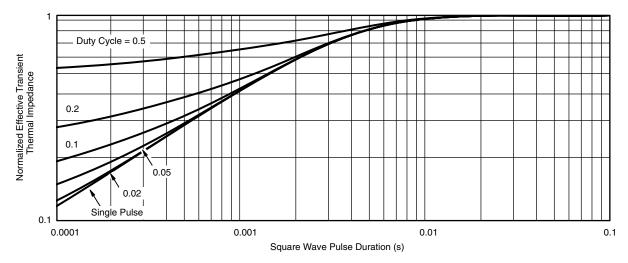


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TYPICAL CHARACTERISTICS (T_J = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



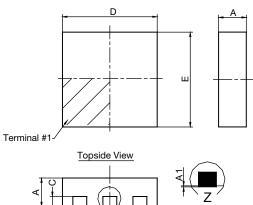
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62991.



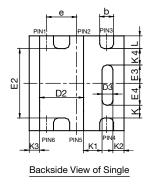
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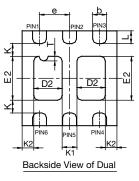
Case Outline for PowerPAK® SC70T



Side View







			SING	LE PAD		DUAL PAD						
DIM.	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	0.525	0.60	0.65	0.0206	0.024	0.026	0.525	0.60	0.65	0.0206	0.024	0.026
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D2	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D3	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E2	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E3	0.345	0.395	0.445	0.014	0.016	0.018						
E4	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC 0.026 BSC		0.65 BSC			0.026 BSC					
K		0.275 TYP.		0.011 TYP.		0.275 TYP.		0.011 TYP.				
K1		0.400 TYP. 0.016 TYP.			0.320 TYP.			0.013 TYP.				
K2		0.240 TYP.		0.009 TYP.		0.252 TYP.		0.010 TYP.				
K3		0.225 TYP.		0.009 TYP.								
K4		0.355 TYP.		0.014 TYP.								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006

Notes

1. All dimensions are in millimeter. Millimeters will govern.

2. Package outline exculsive of mold flash and metal burr.

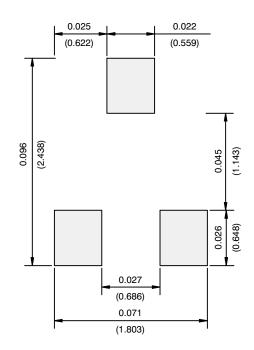
3. Package outline inclusive of plating



Application Note 826

Vishay Siliconix

RECOMMENDED MINIMUM PADS FOR SC-70: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

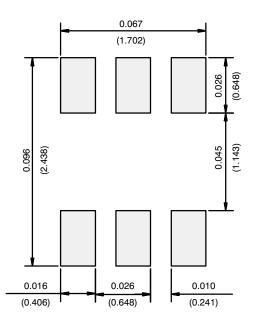
Return to Index

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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